

IN THE CLAIMS:

None of the claims have been amended herein. All of the pending claims 1 through 13 are presented below only for the convenience of the Examiner.

1. (Previously presented) A semiconductor device, comprising:
a semiconductor substrate including an active device region;
at least one conductive line disposed upon the active device region, the at least one conductive line being flanked by sidewall spacers;
an undoped silicon dioxide cap disposed over and in contact with the at least one conductive line;
a passivation layer over the undoped silicon dioxide cap; and
at least one contact aperture defined through the passivation layer and including at least one sidewall extending substantially perpendicularly relative to the semiconductor substrate, at least a portion of the at least one sidewall terminating at an interface between the passivation layer and the undoped silicon dioxide cap.
2. (Previously presented) The semiconductor device of claim 1, wherein the at least one conductive line comprises a word line.
3. (Previously presented) The semiconductor device of claim 1, wherein the passivation layer comprises doped silicon dioxide.
4. (Previously presented) The semiconductor device of claim 1, wherein the passivation layer comprises borophosphosilicate glass, phosphosilicate glass, or borosilicate glass.
5. (Previously presented) The semiconductor device of claim 1, wherein the undoped silicon dioxide cap is at least partially exposed through the at least one contact aperture.

6. (Previously presented) A semiconductor device, comprising:
a semiconductor substrate;
at least one undoped silicon oxide structure; and
at least one doped silicon oxide structure over the at least one undoped silicon oxide structure
and having at least one sidewall substantially perpendicular to a plane of the
semiconductor substrate, at least a portion of the at least one sidewall terminating at an
interface between the at least one doped silicon dioxide structure and the at least one
undoped silicon oxide structure.
7. (Previously presented) The semiconductor device of claim 6, wherein the at least
one sidewall comprises a sidewall of an aperture.
8. (Previously presented) The semiconductor device of claim 6, wherein the at least
one sidewall at least partially defines an aperture through the at least one doped silicon oxide
structure.
9. (Previously presented) The semiconductor device of claim 6, wherein the at least
one doped silicon oxide structure comprises borophosphosilicate glass, phosphosilicate glass, or
borosilicate glass.
10. (Previously presented) The semiconductor device of claim 6, wherein the at least
one undoped silicon oxide structure is at least partially located over a conductive structure.
11. (Previously presented) The semiconductor device of claim 10, wherein the at
least one undoped silicon oxide structure comprises an insulative cap over a conductive line.

12. (Previously presented) The semiconductor device of claim 11, wherein the insulative cap is partially exposed through an aperture of the at least one doped silicon oxide structure defined by the at least one sidewall.

13. (Previously presented) The semiconductor device of claim 6, wherein the at least one undoped silicon oxide structure is at least partially exposed adjacent the at least one sidewall.